



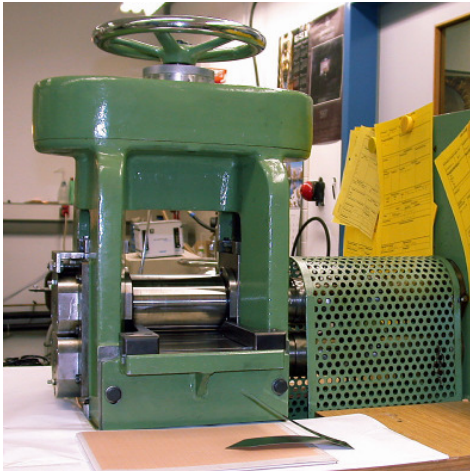
TASCA Target Group – Recent Developments

K. Eberhardt for the TASCA Target Group

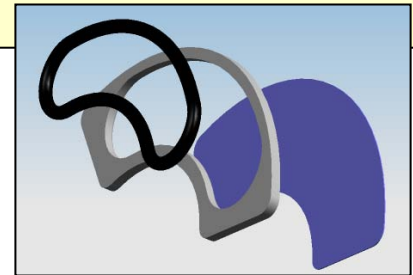
- Target-Backing-Combinations
- In-beam Target Tests
- Electrochemical Deposition



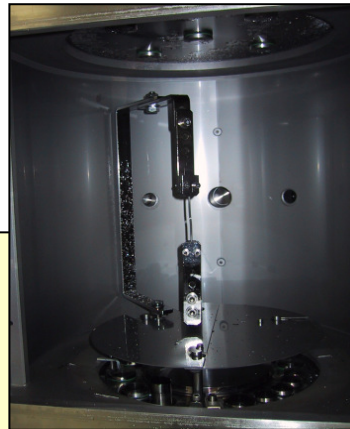
Backing Materials: Be, Al, Ti, C



- Thickness range (Be, Al, Ti): 2-10 μm
- Be: Commercially available
- Al, Ti: Produced by cold rolling and glued to frame (AlMg3)



GSI



- C: Evaporation on betain-saccharose on glass carrier plate.
Thicknesses: 43-50 $\mu\text{g}/\text{cm}^2$



Target-Backing Combinations

- Target material: UF_4 (350-450 $\mu\text{g}/\text{cm}^2$) by evaporation and U (360-420 $\mu\text{g}/\text{cm}^2$) by sputtering
- Backing: Al, Ti, C
- Covering layer: C (10 $\mu\text{g}/\text{cm}^2$, by evaporation)

Sputter target: Depleted $^{\text{nat}}\text{U}$

$^{235}\text{U} < 0.2 \%$

$\varnothing = 1 \text{ ''}$

$d = 3 \text{ mm}$

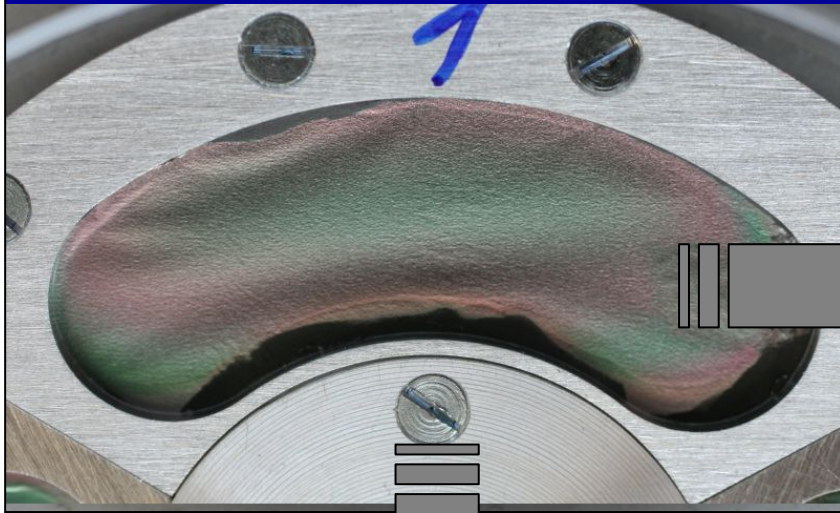
$m \sim 30 \text{ g}$



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Target Tests: ^{12}C - beam / ^{26}Mg -beam on Al/UF_4

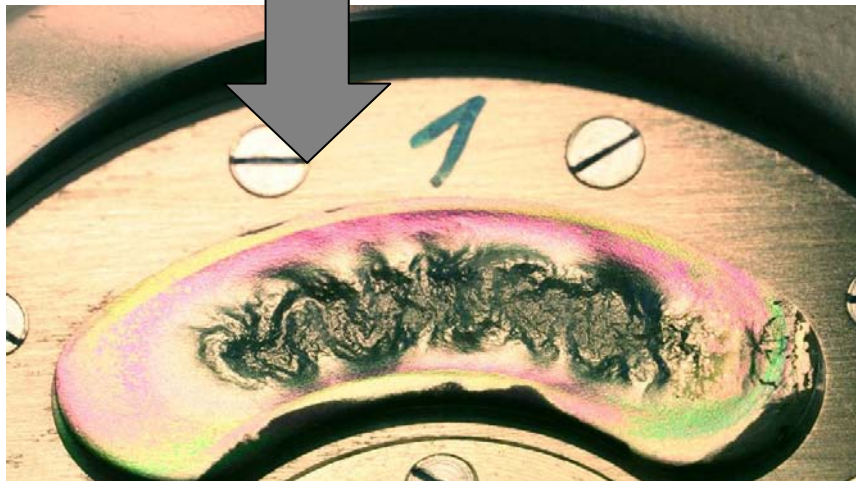
UF_4 on Al, unirradiated



UF_4 on Al after $0.5 \mu\text{A } ^{12}\text{C}$

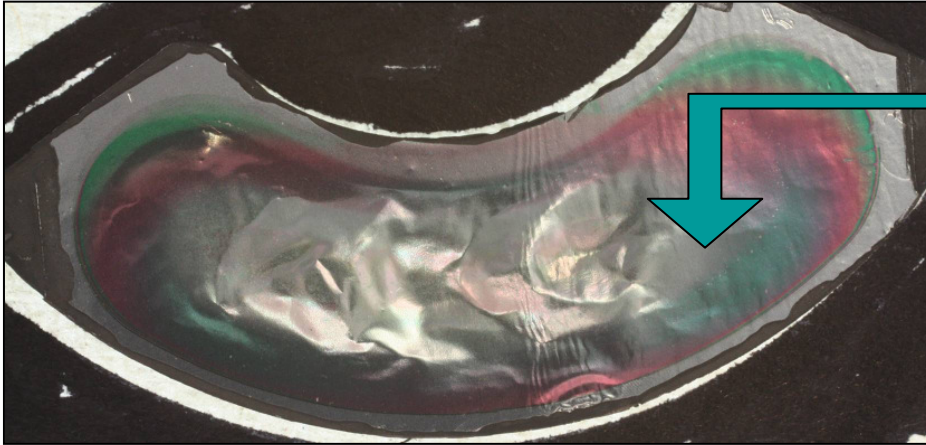
Target with Al-backing destroyed by Mg-beam.

⇒ Ti and C as Backing?



UF_4 on Al after $1 \mu\text{A } ^{26}\text{Mg}$

Target Tests: ^{40}Ar -beam on different backings



0.4 μA on Al/UF4 wavy
0.4 μA on Al unchanged
0.4 μA on Ti unchanged
tarnished colours

0.8 μA on Al little wavy
0.8 μA on Ti unchanged
tarnished colours
0.8 μA on C destroyed
(non heated)

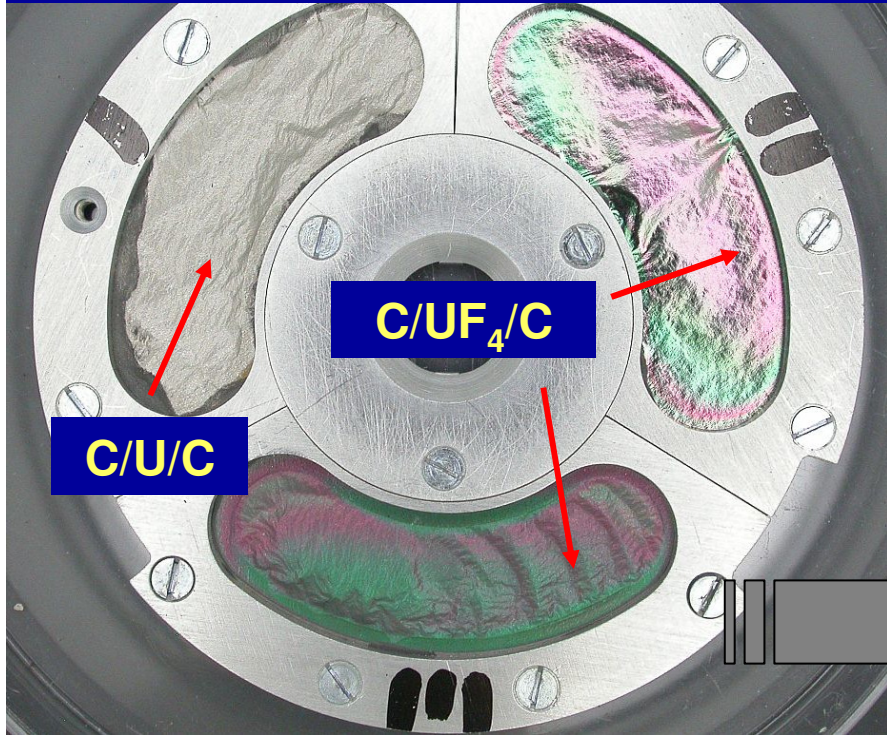


0.8 μA on $\sim 10 \mu\text{m}$ Al holey
0.8 μA on ~ 2.5 Al unchanged

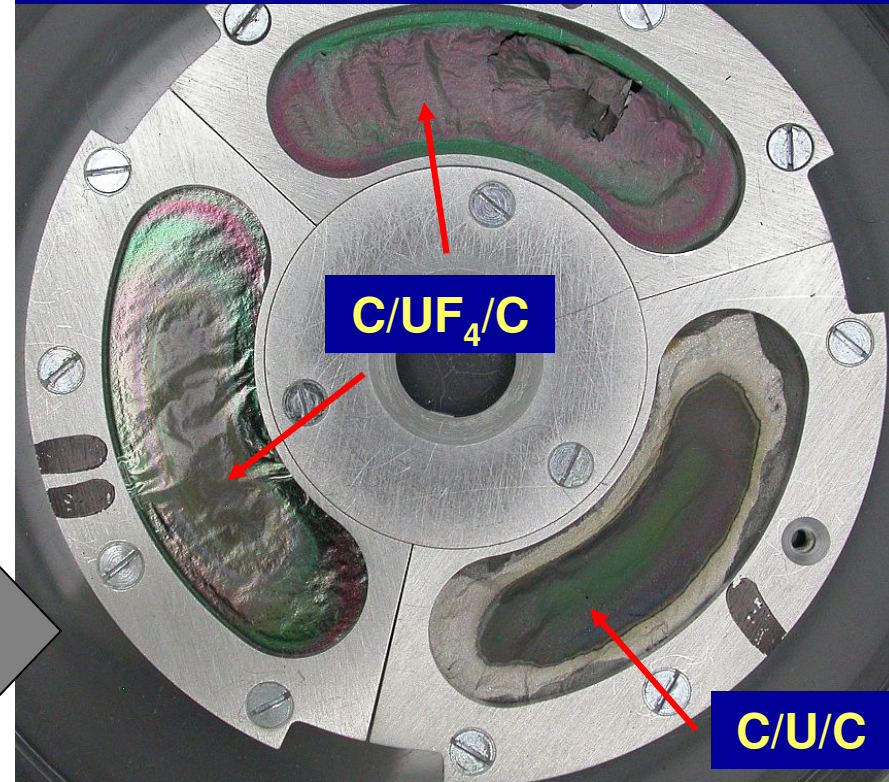
**Irradiation tests only with
backing not sufficient**

Target Tests: ^{26}Mg -beam on C/U/C + C/UF₄/C

unirradiated



After 0.4 μA ^{25}Mg



C/U/C more stable than C/UF₄/C

⇒ Ti as backing material?

GSI

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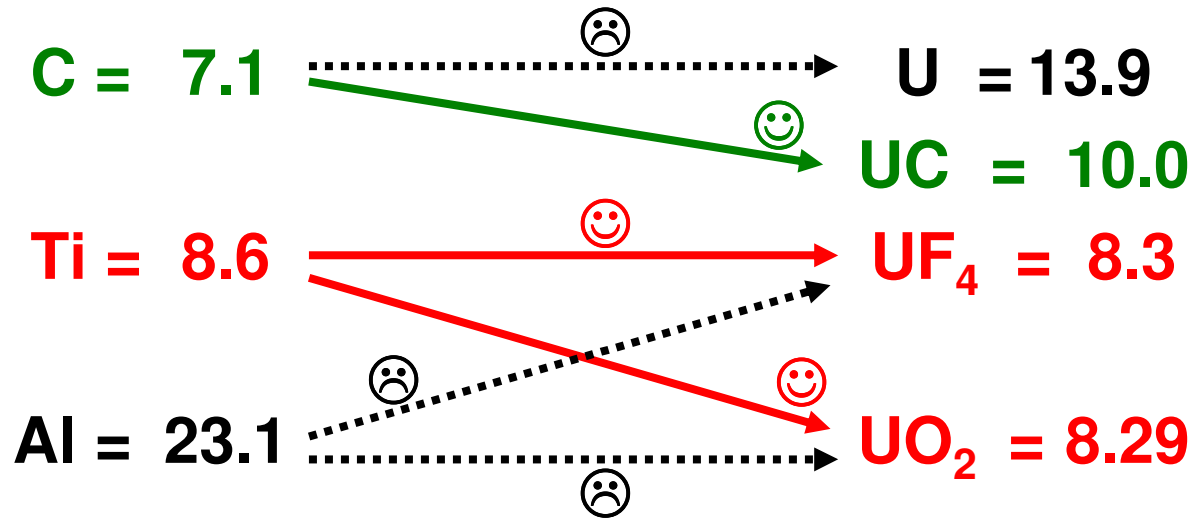


Thermal Expansion of Backing and Target Materials

Thermal expansion coefficient at room temperature
given in $[\mu\text{m}/(\text{m}\cdot\text{K})] = 10^{-6} [1/\text{K}]$

Backing materials

Target materials



Handbook of Physics and Chemistry,
85th edition

Gmelin, Uranium compounds

Future Target Tests (Beam Time November 2006)

C/U/C **40 $\mu\text{g}/\text{cm}^2$ / 400 $\mu\text{g}/\text{cm}^2$ / 10 $\mu\text{g}/\text{cm}^2$**

Ti/U/C **2 μm / 400 $\mu\text{g}/\text{cm}^2$ / 10 $\mu\text{g}/\text{cm}^2$**

Ti/U **2 μm / 400 $\mu\text{g}/\text{cm}^2$**

Ti/¹⁴⁴Sm **2 μm / 100 $\mu\text{g}/\text{cm}^2$**

Ti/¹⁴⁴Sm **2 μm / 450 $\mu\text{g}/\text{cm}^2$**

Ti/¹⁴⁴Sm **2 μm / 800 $\mu\text{g}/\text{cm}^2$**

Ti/¹⁵⁴Sm **2 μm / 450 $\mu\text{g}/\text{cm}^2$**

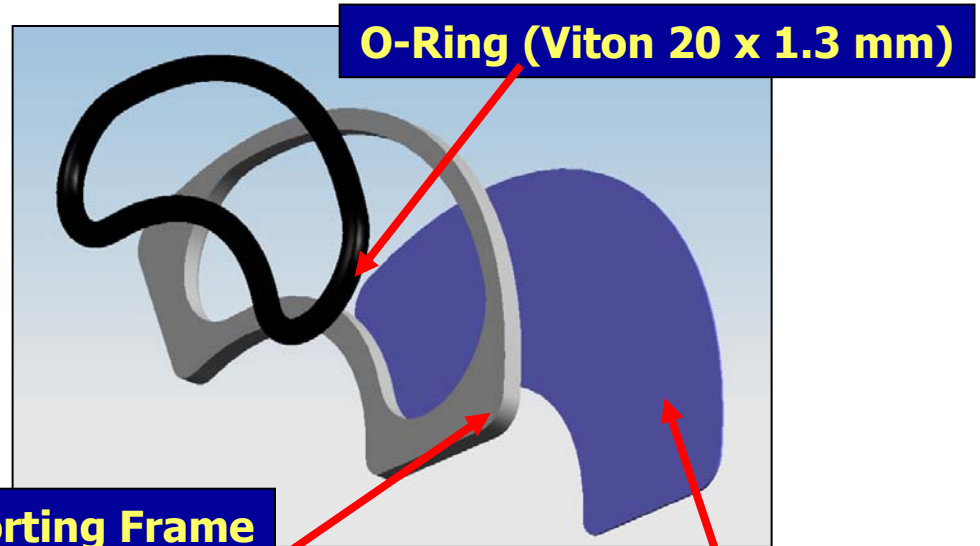
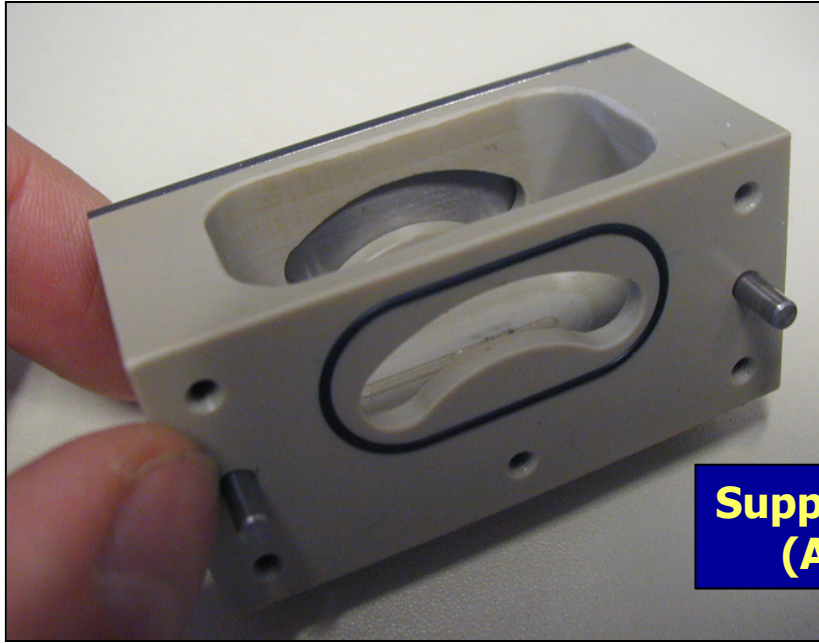
Ti/ ^{nat}Gd **4 μm / 470 $\mu\text{g}/\text{cm}^2$**



C/²⁰⁸PbS/C **40 $\mu\text{g}/\text{cm}^2$ / 470 $\mu\text{g}/\text{cm}^2$ / 10 $\mu\text{g}/\text{cm}^2$**



Electrochemical Deposition – New Plating Cell



**Supporting Frame
(Al 1.0 mm)**

O-Ring (Viton 20 x 1.3 mm)

Backing Foil (Al/Ti/4 – 10 μ m)

- **Material: PEEK**
- **Volume: about 16 ml**
- **Horizontal gaps for electrodes**
- **Uniform electrical field**
- **Water-cooled Ti-blocks as electrodes (not shown)**

Deposition conditions:

Plating time.....5 h
Voltage.....150 V
Current.....100 – 800 μ A
Stirring at.....1000 U/min
Temperature.....15-25 $^{\circ}$ C



Targets Produced

Element	Backing	Amount [µg]	Thickness [µg/cm ²]
Ho	Al	2000	460
Ho	Al	2000	673
Ho	Al	2000	517
Ho	Al	2000	856
Ho	Al	2000	896
Ho	Al	2000	528
Ho	Ti	2000	666
Ho	Ti	2000	517
Ho	Ti	2000	379
Ho	Ti	2000	862
Ho	Ti	2000	701
Ho	Ti	1000	570
Ho	Ti	1000	557
Ho	Ti	1000	568
Ho	Ti	1000	565
Ho	Ti	1000	528
Gd	Ti	1000	517
Gd	Ti	1000	560
Gd	Ti	1000	560
Gd	Ti	1000	557
Gd	Ti	1000	548

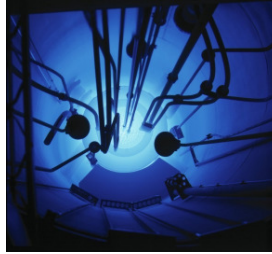
Element	Backing	Amount [µg]	Thickness [µg/cm ²]
Sm	Al	2000	970
Sm	Ti	1000	546
Sm	Al	1000	501
Sm	Al	500	273
Sm	Ti	500	286
Sm	Ti	1500	814
Sm	Al	1500	743
Sm	Al	500	278
Sm	Ti	500	279
Sm	Ti	500	274
Sm	Al	500	258
Sm	Ti	1000	543
Sm	Ti	1000	548
Sm/U	Ti	500 Sm / 500 U	230 Sm / 203 U
Sm/U	Ti	500 Sm / 500 U	245 Sm / 227 U

- Systematic studies
- TASC-Commissioning Experiment May 2006



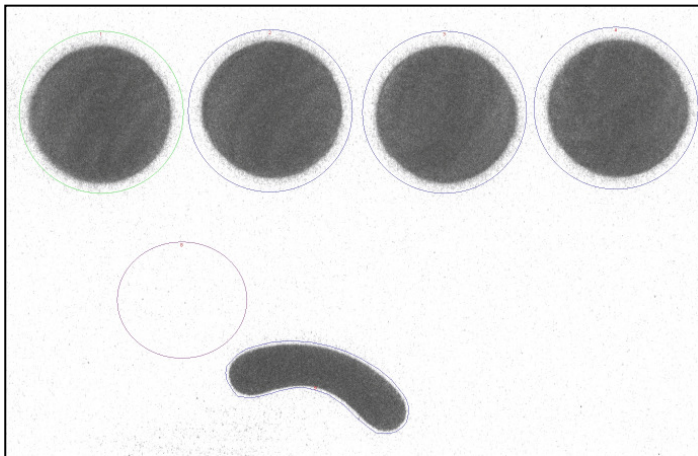
Investigation of the Deposited Layer

Neutron Activation Analysis (NAA) for yield determination

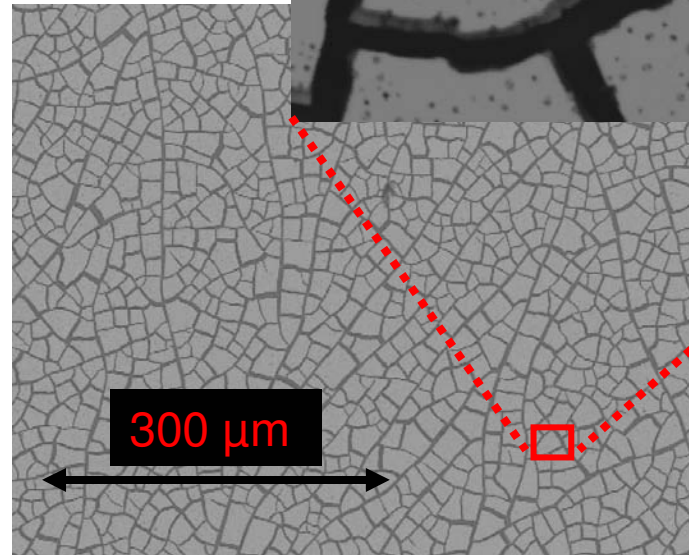
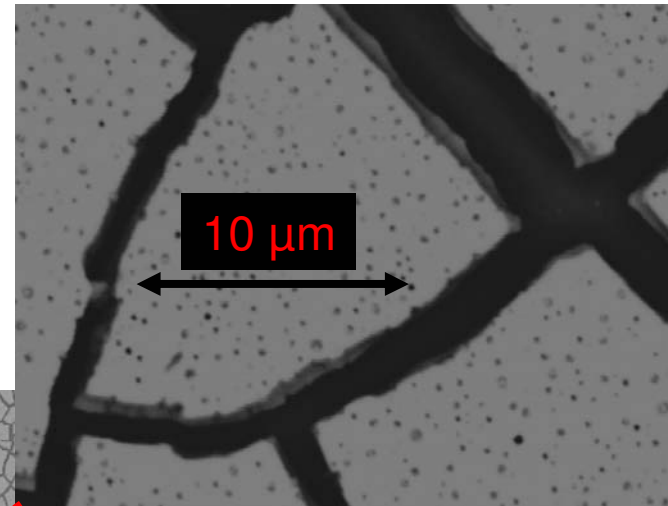


Scanning Electron Microscopy (SEM) and Energy Dispersive X-ray Analysis (EDX) for microstructural analysis

Radiographic Imaging (RI) for yield determination and homogeneity check



RI of U-targets ($\sim 400 \mu\text{g}/\text{cm}^2$)



SEM of U-target ($\sim 380 \mu\text{g}/\text{cm}^2$)

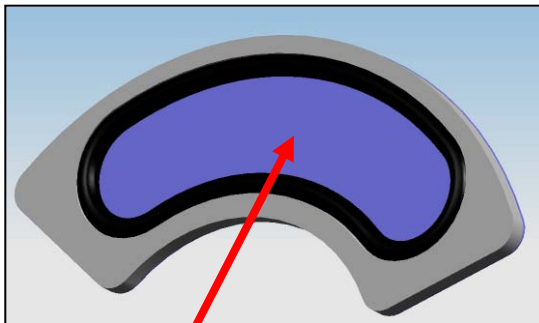
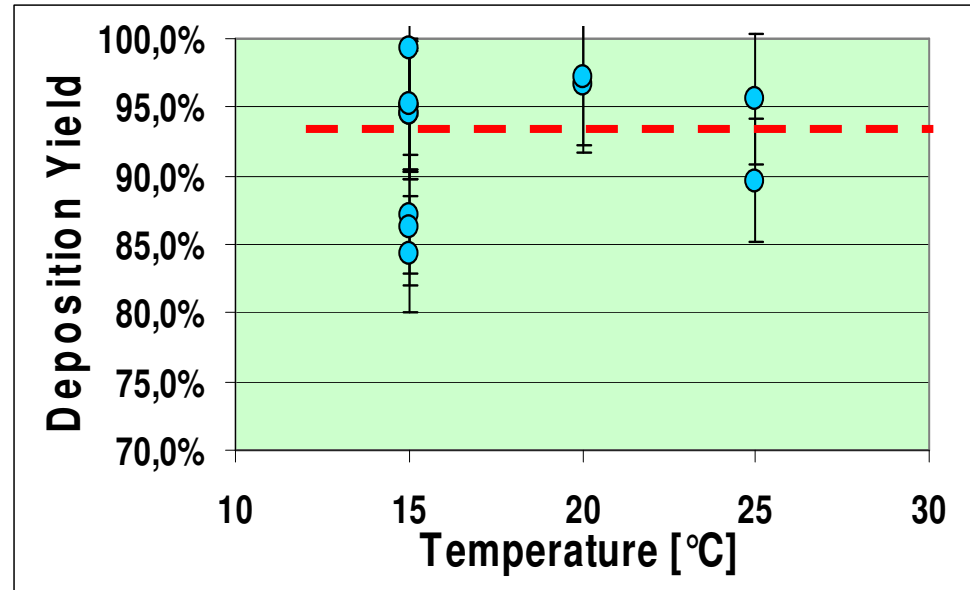
Optimizing the Plating Conditions

Deposition yield as a function of temperature:

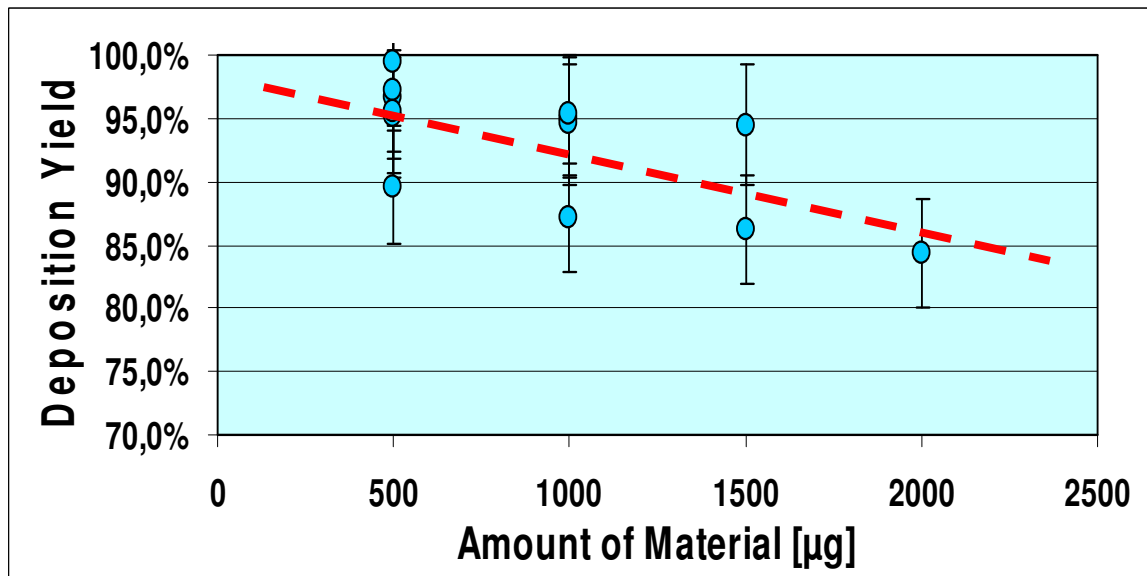
- Yield $\geq 85\%$
- **No correlation** observed

Deposition as a function of the initial amount of material:

- Yield $\geq 85\%$
- **Yield decreases** with initial mass



Target Area: 1.7 cm²



Electrodeposition – Future Investigations

Electrodeposition of other target materials:

Lanthanides + Th, Pu, Cm +.....

Scannin Electron Microscopy (SEM) and Energy Dispersive X-ray Analysis (EDX):

for studies of microstructure and elemental
distribution in “mixed” lanthanide/actinide targets

Radiographic Imaging (RI):

for yield determination and homogeneity check

